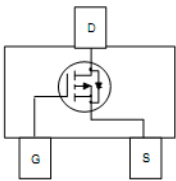
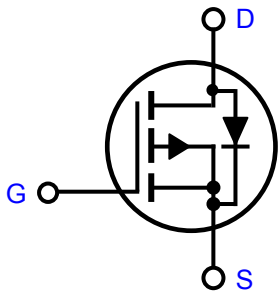
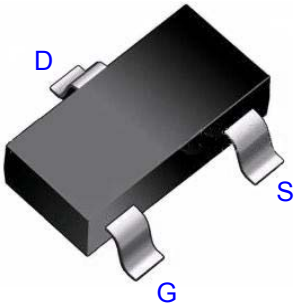



<p>P沟道 增强型 场效应晶体管 P-Channel Enhancement-Mode MOS FETs</p>	<p>HPM2301 P-Channel Enhancement Mode MOS FETs</p> <p>对应其他工业型号 SI2301 AO2301 ME2301 GM2301</p>
<p>Features</p> <ul style="list-style-type: none"> ■ -20V, -2.8A, $R_{DS(ON)}=100m\Omega @ V_{GS}=-10V$ ■ High dense cell design for extremely low $R_{DS(ON)}$ ■ Rugged and reliable ■ Lead free product is acquired ■ SOT-23 Package ■ Marking Code: A1 <p>Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0</p> <div style="text-align: center;">  </div>	

<p>Internal Block Diagram</p> <div style="text-align: center;">  </div> <p>SOT-23 内部结构</p>	<p>HPM2301 (Package: SOT-23)</p> <div style="text-align: center;">  </div> <p>SOT-23 管脚排列</p>	<p>元件标识 (打印)</p> <div style="text-align: center;">  </div> <p>DEVICE MARKING: A1</p>
--	---	--

■ MAXIMUM RATINGS 最大额定值

Characteristic 特性参数	Symbol 符号	Max 最大值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	-20	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 10	
Drain Current (continuous) 漏极电流-连续	I_D	-2.8	A
Drain Current (pulsed) 漏极电流-脉冲	I_{DM}	-10	
Total Device Dissipation 总耗散功率 $T_A=25^\circ C$ (环境温度为25°C)	P_D	900	mW
Junction 结温	T_j	150	°C
Storage Temperature 储存温度	T_{stg}	-55 to +150	
Solder Temperature/Solder Time 焊接温度/焊接时间	T/t	260/10	°C/S

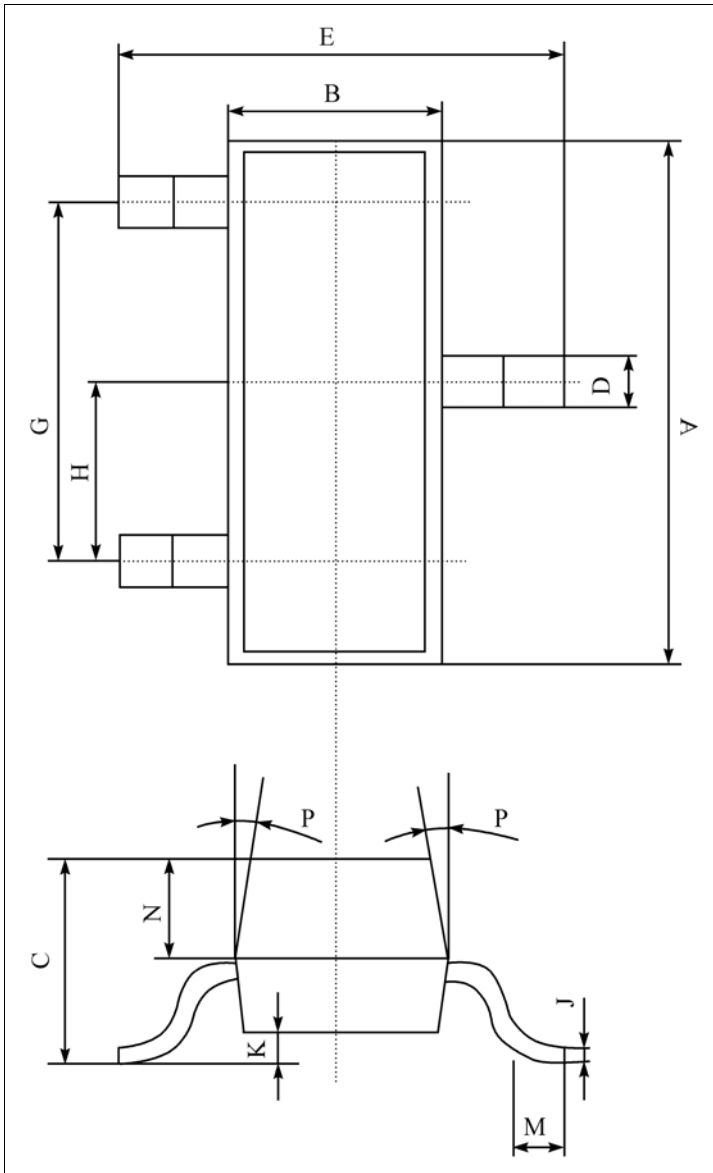
■ ELECTRICAL CHARACTERISTICS 电特性 ($T_A=25^\circ\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压 ($I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$)	BV_{DSS}	-20	--	--	V
Gate Threshold Voltage 栅极开启电压 ($I_D=-250\mu\text{A}$, $V_{GS}=V_{DS}$)	$V_{GS(th)}$	-0.5	--	-1.5	
Diode Forward Voltage Drop 内附二极管正向压降 ($I_S=-0.75\text{A}$, $V_{GS}=0\text{V}$)	V_{SD}	--	--	-1.5	
Zero Gate Voltage Drain Current 零栅压漏极电流	I_{DSS}	$V_{GS}=0\text{V}$, $V_{DS}=-16\text{V}$	--	--	-1
		$V_{GS}=0\text{V}$, $V_{DS}=-16\text{V}$, $T_A=55^\circ\text{C}$	--	--	-5
Gate Body Leakage 栅极漏电流	I_{GSS}	--	--	± 100	nA
Static Drain-Source On-State Resistance 静态漏源导通电阻	$R_{DS(ON)}$	$I_D=-2.8\text{A}$, $V_{GS}=-4.5\text{V}$	--	--	100
		$I_D=-2\text{A}$, $V_{GS}=-2.5\text{V}$	--	--	120
Input Capacitance 输入电容 ($V_{GS}=0\text{V}$, $V_{DS}=-10\text{V}$, $f=1\text{MHz}$)	C_{ISS}	--	600	--	pF
Common Source Output Capacitance 共源输出电容 ($V_{GS}=0\text{V}$, $V_{DS}=-10\text{V}$, $f=1\text{MHz}$)	C_{OSS}	--	120	--	
Turn-ON Time 开启时间 ($V_{DS}=-10\text{V}$, $I_D=-2.8\text{A}$, $R_{GEN}=6\Omega$)	$t_{(on)}$	--	8	--	nS
Turn-OFF Time 关断时间 ($V_{DS}=-10\text{V}$, $I_D=-2.8\text{A}$, $R_{GEN}=6\Omega$)	$t_{(off)}$	--	60	--	

Pulse Width $\leq 300\mu\text{s}$; Duty Cycle $\leq 2.0\%$

■ DIMENSION 外形封装尺寸数据

Package: SOT-23 HAOHAI Package Code: MM



序号	数值及公差
A	2.90±0.10
B	1.30±0.10
C	1.00±0.10
D	0.40±0.10
E	2.40±0.20
G	1.90±0.10
H	0.95±0.05
J	0.13±0.05
K	0.00-0.10
M	≥0.20
N	0.60±0.10
P	7±2°

Packing
 Tape & Reel, 3Kpcs/Reel
 SOT-23 包装规格
 SMD片式表面贴封装
 包装方式: 载带卷盘包装
 每卷数量3000只 (3Kpcs/Reel)
 每盒数量30000只 (30Kpcs/BOX)
 每箱数量300000只 (300Kpcs/Cartons)



经中华人民共和国工商行政管理总局商标局批准

HAOHAI、HHE 图案、字母、均为我公司正式注册商标，仿冒、盗用均属侵权，违法必究！

WARN: Letters, patterns, are officially registered my trademark counterfeiting, theft are all violations, violators will be held liable !

深圳市浩海电子有限公司

SHENZHEN HAOHAI ELECTRONICS CO., LTD.2 floor(whole floor), BAOXIN Building. 0 Lane on the 8th. Yufeng Garden.
82 District. BAOAN District, Shenzhen City, Guangdong Province, China.公司电话 TEL: +86-755-29955080、29955081、29955082、29955083
总机八线 29955090、29955091、29955092、29955093

FAX: +86-755-27801767

E-mail: kkg@kkg.com.cn产品主页 <http://www.szhhe.com><http://www.kkg.com.cn>